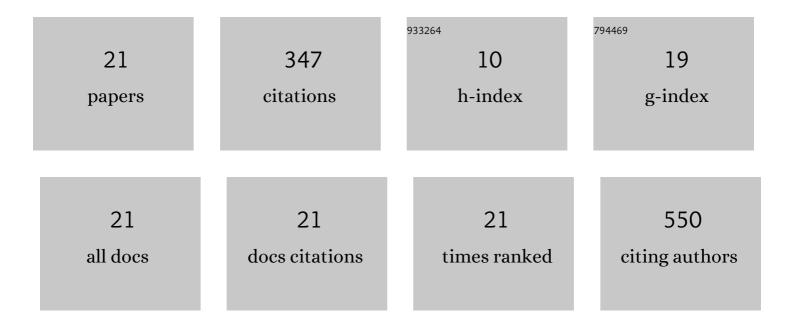
Simon Hammersley

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/3206858/publications.pdf

Version: 2024-02-01



#	Article	IF	CITATIONS
1	Carrier dynamics at trench defects in InGaN/GaN quantum wells revealed by time-resolved cathodoluminescence. Nanoscale, 2022, 14, 402-409.	2.8	13
2	GaN surface sputter damage investigated using deep level transient spectroscopy. Materials Science in Semiconductor Processing, 2021, 126, 105654.	1.9	2
3	Effect of Si-doped InGaN underlayers on photoluminescence efficiency and recombination dynamics in InGaN/GaN quantum wells. Journal Physics D: Applied Physics, 2021, 54, 475104.	1.3	2
4	Optical properties of c-Plane InGaN/GaN single quantum wells as a function of total electric field strength. Japanese Journal of Applied Physics, 2019, 58, SCCB09.	0.8	5
5	Optical and structural properties of dislocations in InGaN. Journal of Applied Physics, 2019, 125, .	1.1	11
6	Effect of stacking faults on the photoluminescence spectrum of zincblende GaN. Journal of Applied Physics, 2018, 123, .	1.1	10
7	Photoluminescence studies of cubic GaN epilayers. Physica Status Solidi (B): Basic Research, 2017, 254, 1600733.	0.7	16
8	Comparative studies of efficiency droop in polar and non-polar InGaN quantum wells. Applied Physics Letters, 2016, 108, .	1.5	18
9	A comparison of the optical properties of InGaN/GaN multiple quantum well structures grown with and without Si-doped InGaN prelayers. Journal of Applied Physics, 2016, 119, .	1.1	13
10	Diatom Frustules as a Biomineralized Scaffold for the Growth of Molybdenum Disulfide Nanosheets. Chemistry of Materials, 2016, 28, 5582-5586.	3.2	13
11	Effect of QW growth temperature on the optical properties of blue and green InGaN/GaN QW structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 209-213.	0.8	5
12	Room temperature PL efficiency of InGaN/GaN quantum well structures with prelayers as a function of number of quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 248-251.	0.8	7
13	Effect of electron blocking layers on the conduction and valence band profiles of InGaN/GaN LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 262-265.	0.8	1
14	Effects of quantum well growth temperature on the recombination efficiency of InGaN/GaN multiple quantum wells that emit in the green and blue spectral regions. Applied Physics Letters, 2015, 107, .	1.5	58
15	Supplemental Blue LED Lighting Array to Improve the Signal Quality in Hyperspectral Imaging of Plants. Sensors, 2015, 15, 12834-12840.	2.1	24
16	Investigation of unintentional indium incorporation into GaN barriers of InGaN/GaN quantum well structures. Physica Status Solidi (B): Basic Research, 2015, 252, 928-935.	0.7	15
17	Carrier distributions in InGaN/GaN lightâ€emitting diodes. Physica Status Solidi (B): Basic Research, 2015, 252, 890-894.	0.7	6
18	On the origin of blue-green emission from heteroepitaxial nonpolar a-plane InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 465-468	0.8	4

#	ŧ	Article	IF	CITATIONS
1	19	The consequences of high injected carrier densities on carrier localization and efficiency droop in InGaN/GaN quantum well structures. Journal of Applied Physics, 2012, 111, .	1.1	105
2	20	Study of efficiency droop and carrier localisation in an InGaN/GaN quantum well structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2194-2196.	0.8	16
2	21	Carrier dynamics in non-polar GaN/AlGaN quantum wells intersected by basal-plane stacking faults. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1894-1896.	0.8	3